

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5732009 A	19980324	21	Semiconductor integrated circuit device including a DRAM in which a cell selection transistor has a stabilized threshold voltage	365/51	257/296; 257/300	Tadaki, Yoshitaka et al.
2	US 5661344 A	19970826	8	Porous dielectric material with a passivation layer for electronics applications	257/758	257/637; 257/642; 257/759; 257/760	Havemann, Robert H. et al.
3	US 5612254 A	19970318	15	Methods of forming an interconnect on a semiconductor substrate	438/634	438/631; 438/637; 438/672; 438/675	Mu, Xiao-Chun et al.
4	US 5573965 A	19961112	8	Method of fabricating semiconductor devices and integrated circuits using sidewall spacer technology	438/297	438/305; 438/595	Chen, Min-Liang et al.
5	US 5061985 A	19911029	15	Semiconductor integrated circuit device and process for producing the same	257/751	257/754; 257/758; 257/761; 257/764; 257/765	Meguro, Hideo et al.